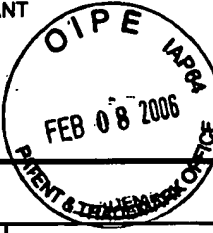


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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT: Leonard F rbes, et al.			
					FILING DATE January 5, 2001		GROUP 2823	
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FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
	AN						Yes	No
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
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EXAMINER		DATE CONSIDERED						
/Khien Nguyen/		06/20/2006						
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ATTY. DOCKET NO.
M122-1531

SERIAL NO.
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APPLICANT
Micron Technology, Inc.

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.		09/755673	
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U.S. PATENT DOCUMENTS							
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	AA						
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U.S. PATENT DOCUMENTS							
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Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
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EXAMINER K. N. Nguyen				DATE CONSIDERED 08/16/02			
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